

AN 1997-122301 [12] WPIX Full-text

DNN N1997-100597 DNC C1997-039525

TI **Measurement** of exhaust gas from internal combustion engine -
includes using heated metal oxide semiconductor changing resistance with
oxygen **concentration**.

DC E36 H06 J04 L03 S02 S03 X22

PA (NITS) NGK SPARK PLUG CO LTD

CYC 1

PI JP--09005273 A 19970110 (199712)* 29p G01N-027-12 <--

ADT JP--09005273 A 1995JP-0176668 19950619

PRAI 1995JP-0176668 19950619

IC ICM G01N-027-12

AB ~~JP-09005273~~ A UPAB: 19970320

A gas sensor (46) comprises a metallic oxide semiconductor the resistance value of which is changed according to oxygen **concn**; and a heater (75) arranged near the metallic oxide semiconductor. By **measuring** the resistance value of the metallic oxide semiconductor by applying an AC voltage on the metallic oxide semiconductor, the gas component **concn** in exhaust gas is **measured**.

ADVANTAGE - Deterioration due to migration of a metallic oxide semiconductor in high temp gas does not occur.

Dwg. 5/32

FS CPI EPI

FA AB; GI; DCN

MC CPI: E11-Q03J; H06-C04; J04-C04; L03-E05C; L03-H05

EPI: S02-J01A; S03-E02A; X22-A05B